



Docket:
90065.141001/17732.6317.003

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3.27.03
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IN THE UNITED STATES PATENT & TRADEMARK OFFICE

Applicant:	Christopher B. Kocon, et al.)	Examiner:	
)	Paul E.	
Serial No.:	10/039,319)	Brock II	
)		
Filed:	November 9, 2001)	Art Unit:	
)	2815	
For:	MOS GATED DEVICE HAVING A BURIED GATE AND PROCESS FOR FORMING SAME)		
)		

RESPONSE TO OFFICE ACTION

Assistant Commissioner for Patents
Washington, DC 20231

Dear Sir:

RECEIVED
MAR 19 2003
TECHNOLOGY CENTER 2800

Introduction

This amendment cancels claims 24, 26, 32 and 33 without prejudice. It amends claim 21 to add a limitation that the depth of the source regions is substantially coplanar with the level of the conductive gate material. Claims 29 and 30 are amended to make them consistent with the elected species. New claims 40 and 41 define a process that excludes doped insulation layers and expressly requires ion implantation and diffusion for the source and body dopants.